

Docket No.: 61352-041



**PATENT**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of	:	Customer Number: 20277
Hiroyuki FURUYA, et al.	:	Confirmation Number: 2093
Serial No.: 10/620,432	:	Group Art Unit: 2812
Filed: July 17, 2003	:	Examiner:
For:	:	
METHOD OF FABRICATING NITRIDE BASED SEMICONDUCTOR SUBSTRATE AND METHOD OF FABRICATING NITRIDE BASED SEMICONDUCTOR DEVICE		

**INFORMATION DISCLOSURE STATEMENT**

Mail Stop Missing Parts  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached form PTO-1449. It is respectfully requested that the references be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is being filed within three months of the U.S. filing date OR before the mailing date of a first Office Action on the merits. No certification or fee is required.

Each non-English language reference was first cited in a corresponding foreign application search report or office action. A copy of the foreign search report or office action, together is attached for the Examiner's information.

The relevance of "InGaN/GaN/AlGaIn-based laser diodes grown on epitaxially laterally overgrown GaN" and "High-Power; Long-Lifetime InGaN/GaN/AlGaIn-Based Laser Diodes Grown on Pure GaN Substrates" is discussed on pages 3 and 4 of the present specification.

Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account 500417 and please credit any excess fees to such deposit account.

Respectfully submitted,

MCDERMOTT, WILL & EMERY



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**Date: December 18, 2003**



SHEET 1 OF 1

<b>INFORMATION DISCLOSURE CITATION IN AN APPLICATION</b>  <b>(PTO-1449)</b>				ATTY. DOCKET NO. <b>61352-041</b>		SERIAL NO. <b>10/620,432</b>	
				APPLICANT <b>Hiroyuki FURUYA, et al.</b>			
				FILING DATE <b>July 17, 2003</b>		GROUP <b>2812</b>	

FOREIGN PATENT DOCUMENTS							
EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes -Number + -Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation	
						Yes	No
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		EP 1 278 233 A1 (WO 01/084608)	01/22/2003	TOYODA GOSEI CO., LTD.			
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OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)			
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	
		I. KIDOGUCHI et al., "Improvement of Crystalline Quality in GaN Films by Air-Bridged Lateral Epitaxial Growth", Jpn. J. Appl. Phys., Part 2, Vol. 39, No. 5B, (2000), pages L453-456.	
		S. NAKAMURA, "InGaN/GaN/A1GaN-based laser diodes grown on epitaxially laterally overgrown GaN", Journal of Materials Research, Commentaries and Reviews, Vol. 14, No. 7, July 1999, pages 2716-2731.	
		S. NAKAMURA et al., "High-Power, Long-Lifetime InGaN/GaN/A1GaN-Based Laser Diodes Grown on Pure GaN Substrates", Jpn. J. Appl. Phys., Vol. 37, 15 March 1998, pages L309-L312.	

EXAMINER	DATE CONSIDERED
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.